UNISONIC TECHNOLOGIES CO., LTD

UPG50N120

Insulated Gate Bipolar Transistor

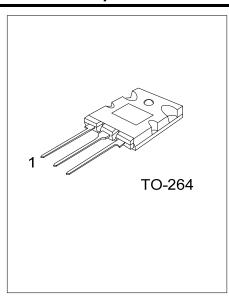
1200V NPT PLANAR IGBT

DESCRIPTION

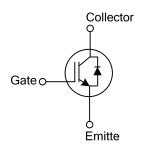
The UTC **UPG50N120** is a 1200V NPT Planar Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to offers superior conduction and switching performance, high avalanche ruggedness and easy parallel operation.

■ FEATURES

- * High speed switching
- * High input impedance
- * Low saturation voltage: V_{CE(SAT)} =2.6V @ I_C=50A



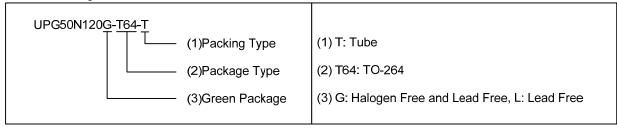
■ SYMBOL



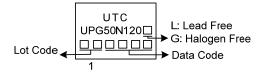
ORDERING INFORMATION

Ordering Number		Dealtone	Pin Assignment			Deelsing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UPG50N120L-T64-T	UPG50N120G-T64-T	TO-264	G	С	E	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



MARKING



<u>www.unisonic.com.tw</u> 1 of 3

ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V_{CES}	1200	V
Gate-Emitter Voltage		$V_{\sf GES}$	±25	V
Continuous Collector Current	T _C =25°C	Ic	100	Α
	T _C =100°C		50	Α
Collector Current Pulsed (Note 1)		I _{CM}	160	Α
Power Dissipation		P_D	500	W
Operating Junction Temperature		T_J	-55 ~ + 150	°C
Storage Temperature Range		T _{STG}	-55 ~ + 150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

THERMAL CHARACTERISTICS

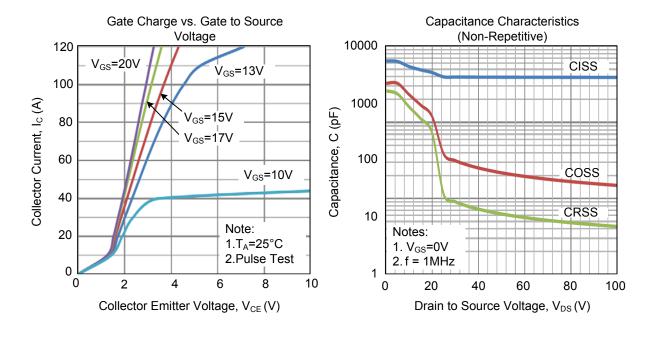
PARAMETER	SYMBOL RATINGS		UNIT	
Junction to Ambient	θ_{JA}	25	°C/W	
Junction to Case	θ_{JC}	0.25	°C/W	

ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	MIN	TYP	MAX	UNIT	
Off Characteristics							
Collector-Emitter Breakdown Voltage	B _{VCES}	I _C =1mA, V _{GE} =0V		1200			V
Collector Cut-Off Current	I _{CES}	V _{CE} =V _{CES} , V _{GE} =0V				1	mΑ
G-E Leakage Current	I _{GES}	V _{GE} =V _{GES} , V _{CE} = 0V				±250	mΑ
On Characteristics							
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	I _C =250μA, V _{CE} =V _{GE}		3.5	5.5	7.5	V
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =50A, V _{GE} =15V			2.4	2.6	V
Dynamic Characteristics							
Input Capacitance	C _{IES}				3930		pF
Output Capacitance	C _{OES}	V _{CE} =30V, V _{GE} =0V, f=1MHz			310		pF
Reverse Transfer Capacitance	C _{RES}				95		pF
Switching Characteristics							
Total Gate Charge	Q_G				230		nC
Gate-Emitter Charge	Q_GE	V _{CE} =400V, I _C =64A, V _{GE} =15V			64		nC
Gate-Collector Charge	Q_GC				120		nC
Turn-On Delay Time	t _{D(ON)}				32		ns
Rise Time	t _R	V_{CC} =400V, I_{C} =50A, R_{G} =10 Ω , V_{GE} =15V			37		ns
Turn-Off Delay Time	t _{D(OFF)}				200		ns
Fall Time	t _F				134		ns
SOURCE- DRAIN DIODE RATINGS AN	D CHARACTE	RISTICS					
Forward Voltage Drop	V_{FM}	I _F =50A	T _C =25°C		1.6	4.0	V
Reverse Recovery Time	t _{rr}	I _F =30A,	T _C =25°C		510		ns
Reverse Recovery Charge	Q _{rr}	dI/dt=200A/μS	T _C =25°C		5.5		μC
	-jK	I _F =30A, dl/dt=200A/μS	1688.00	iu.			
UNISONIC TECHNOLOG www.unisonic.com.tw	IES CO., LTD					2W-R20	2 of 3 3-055.B

^{2.} Pulse width limited by maximum junction temperature.

■ TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.